



## N-Channel 30-V (D-S) MOSFET

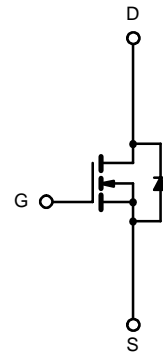
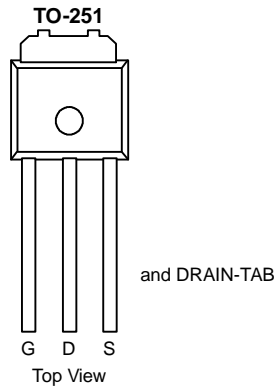
PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>b</sup>
30	0.0095 @ $V_{GS} = 10$ V	63 <sup>b</sup>
	0.014 @ $V_{GS} = 4.5$ V	52 <sup>b</sup>

### FEATURES

- TrenchFET® Power MOSFET
- Optimized for High- or Low-Side

### APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



Order Number: SUU50N03-09P  
SUU50N03-09P—E3 (Lead (Pb)-Free)

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_C = 25^\circ\text{C}$	$I_D$	63 <sup>b</sup>	A
	$T_C = 100^\circ\text{C}$		44.5 <sup>b</sup>	
Pulsed Drain Current		$I_{DM}$	50	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	10	
Avalanche Current	L = 0.1 mH	$I_{AS}$	35	mJ
Single Pulse Avalanche Energy		$E_{AS}$	61	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	$P_D$	65.2	W
	$T_A = 25^\circ\text{C}$		7.5 <sup>a</sup>	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10$ sec	$R_{thJA}$	16	20	$^\circ\text{C/W}$
	Steady State		40	50	
Maximum Junction-to-Case		$R_{thJC}$	1.8	2.3	

Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10$  sec.  
b. Based on maximum allowable Junction Temperature, package limitation current is 50 A.



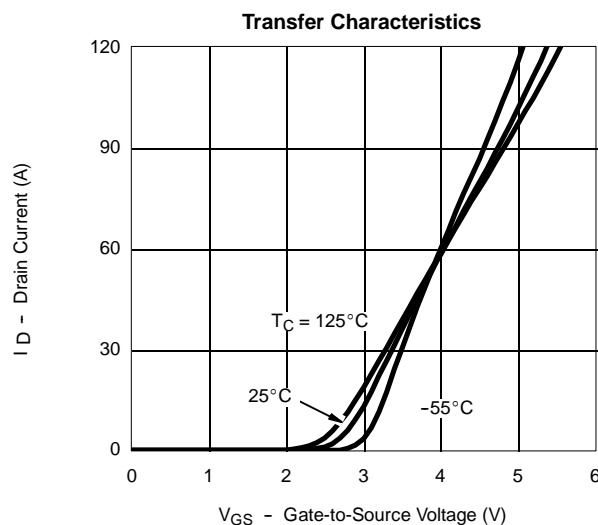
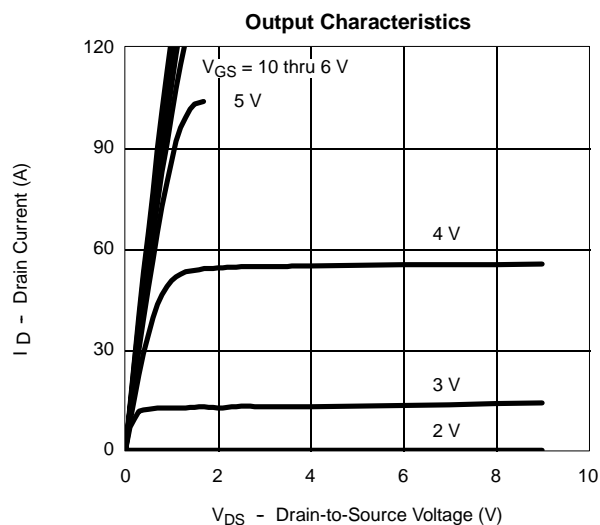
### SPECIFICATIONS ( $T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ <sup>a</sup>	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1.0		3.0	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			50	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance <sup>b</sup>	$r_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0076	0.0095	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125^\circ\text{C}$			0.015	
		$V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		0.0115	0.014	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 20\text{ A}$	20			S
<b>Dynamic<sup>a</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2200		pF
Output Capacitance	$C_{oss}$			410		
Reverse Transfer Capacitance	$C_{rss}$			180		
Gate Resistance	$R_g$			1.5		$\Omega$
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 50\text{ A}$		15	23	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			7.5		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			5.0		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 0.3\ \Omega$ $I_D \cong 50\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\ \Omega$		9	15	ns
Rise Time <sup>c</sup>	$t_r$			80	120	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			22	35	
Fall Time <sup>c</sup>	$t_f$			8	12	
<b>Source-Drain Diode Ratings and Characteristic (<math>T_C = 25^\circ\text{C}</math>)</b>						
Pulsed Current	$I_{SM}$				100	A
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	$I_F = 50\text{ A}, V_{GS} = 0\text{ V}$		1.2	1.5	V
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 50\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		35	70	ns

#### Notes

- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

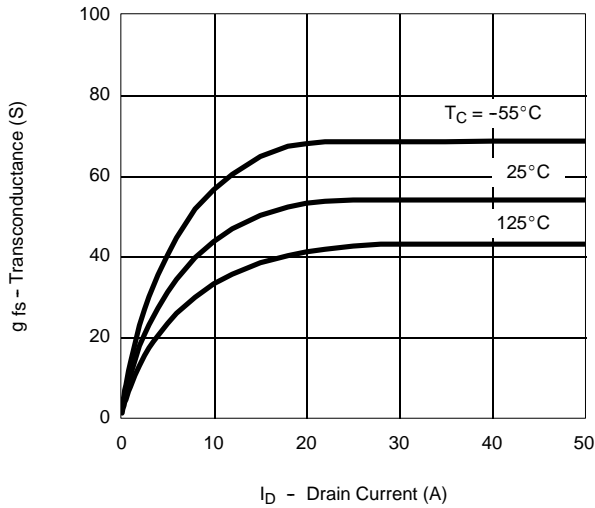
### TYPICAL CHARACTERISTICS ( $25^\circ\text{C}$ UNLESS NOTED)



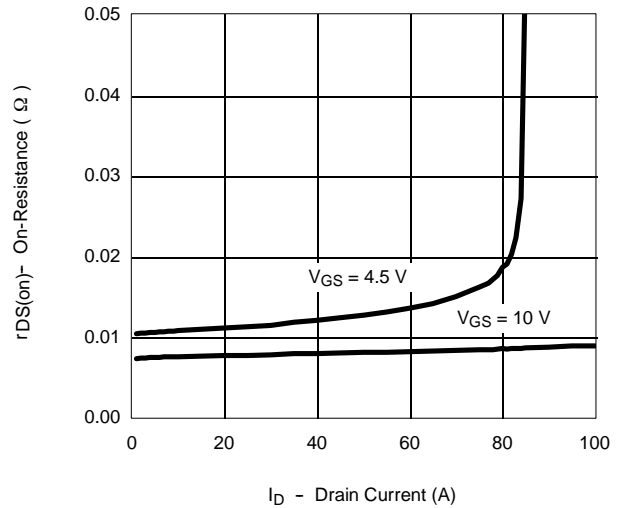


**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

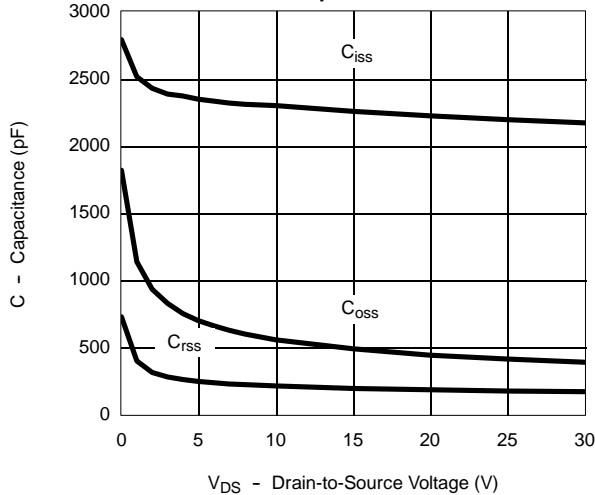
**Transconductance**



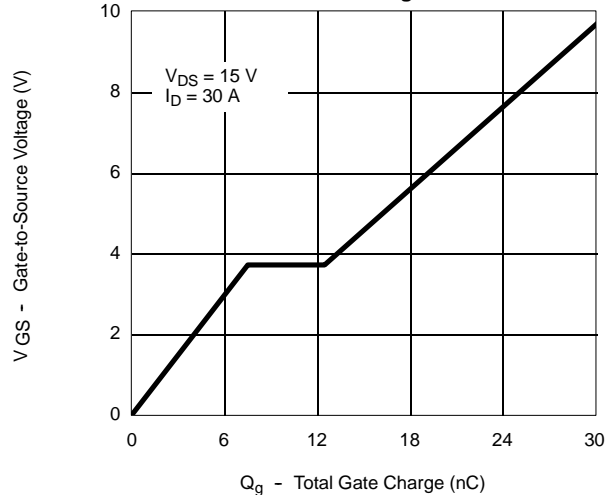
**On-Resistance vs. Drain Current**



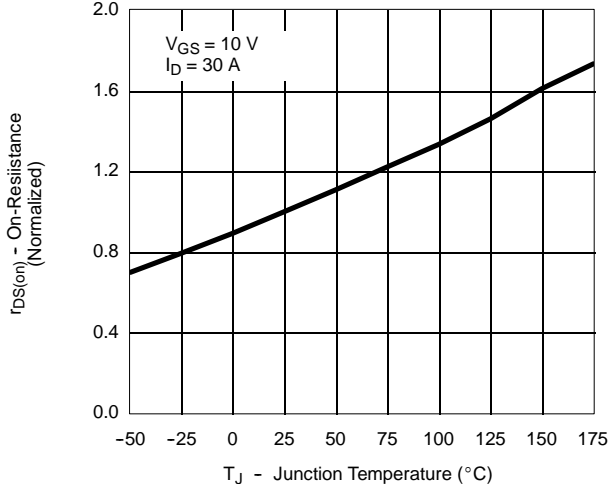
**Capacitance**



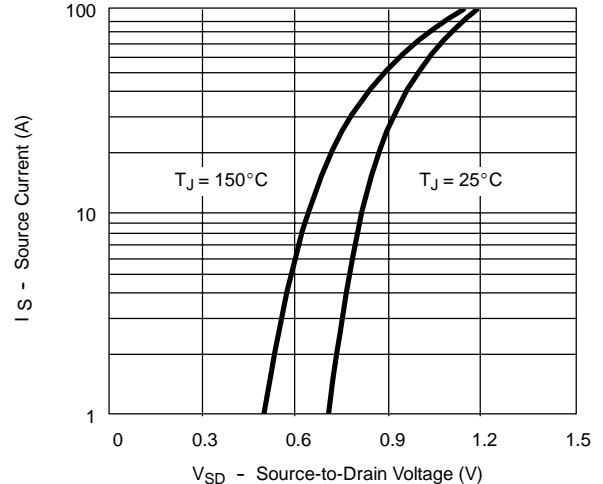
**Gate Charge**



**On-Resistance vs. Junction Temperature**

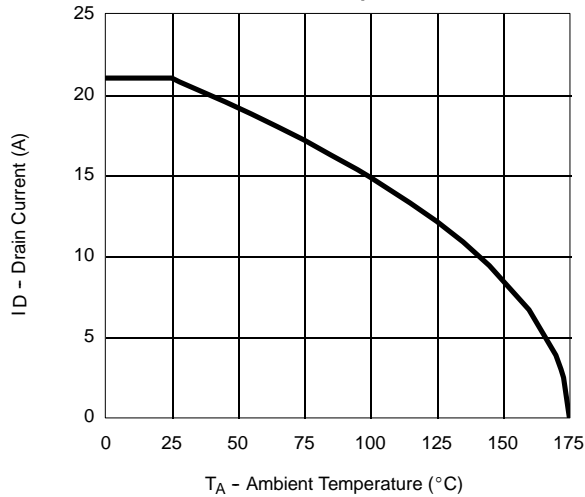


**Source-Drain Diode Forward Voltage**

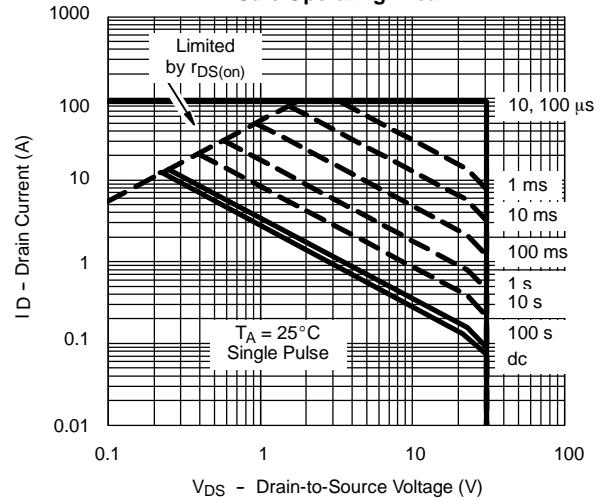


**THERMAL RATINGS**

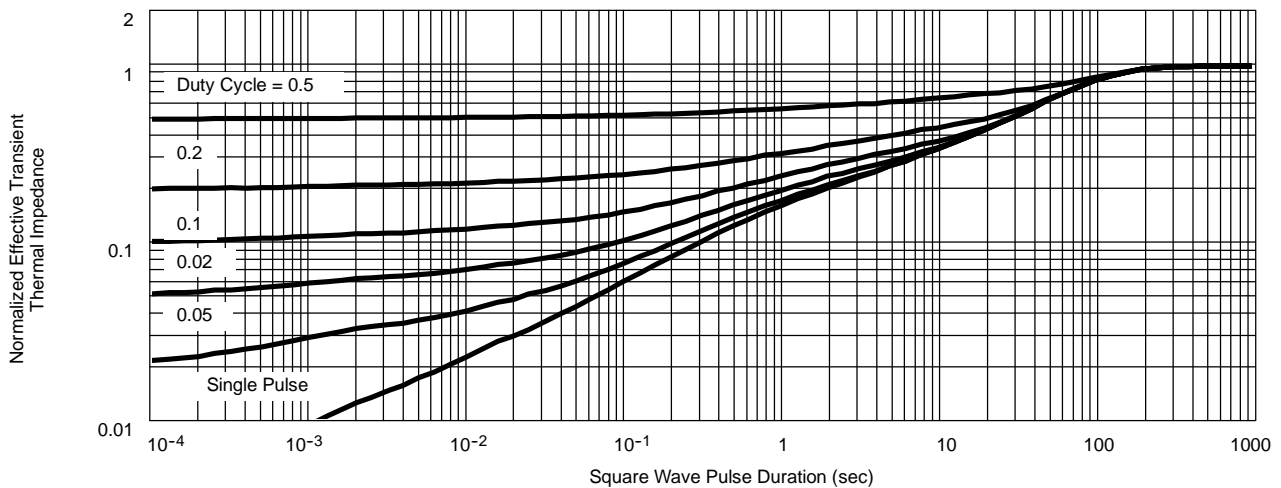
Maximum Drain Current vs. Ambient Temperature



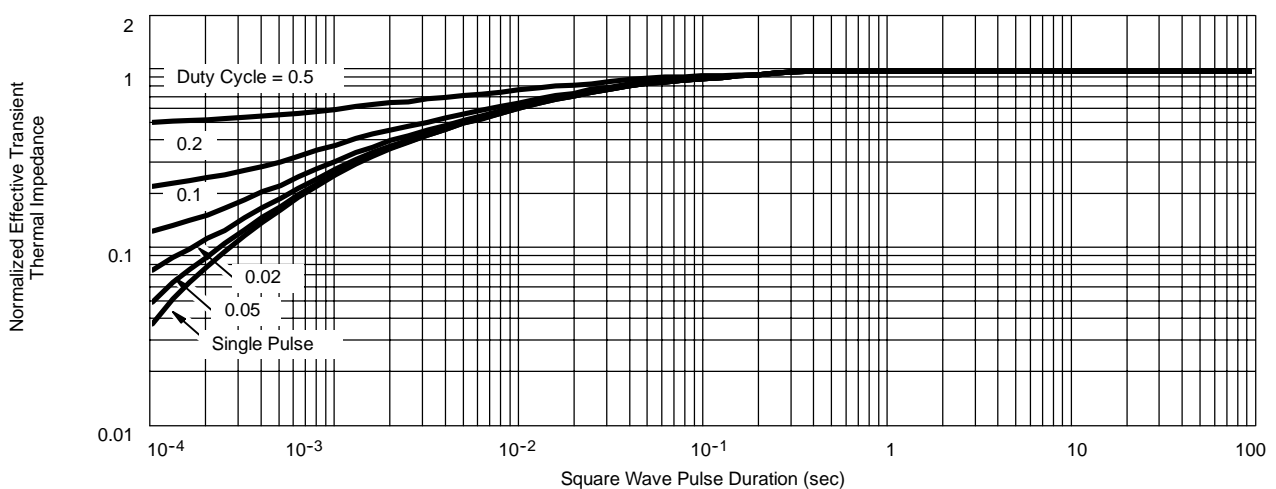
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case





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